

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: **Xiang, et al.**

Serial No.: **10/643,461**

Filed: **August 18, 2003**

For: **Field Effect Transistor Having Increased Carrier Mobility**

Art Unit: **2815**

Examiner: **Nguyen, Joseph H.**

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INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir/Madam:

In this Information Disclosure Statement and pursuant to 37 C.F.R. §§ 1.56 and 1.97, Applicants hereby disclose to the Patent Office patents, publications or other information of which Applicants are aware. A copy of a Form 1449 identifying the patents and other materials is submitted herewith.

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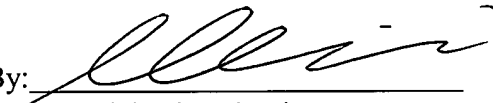
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In accordance with 37 C.F.R. § 1.97(c)(2) and §1.17, a Credit Card Payment Form PTO-2038 for \$180.00 is enclosed to cover the fee for filing this Information Disclosure Statement, since it is being filed after the mailing date of a final action. Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.


The Assistant Commissioner is hereby authorized to charge or credit Deposit Account Number 50-0731 for any deficiency or overpayment in the fees required for the filing of this Information Disclosure Statement, for which purpose a duplicate copy of this paper is also included.

Respectfully submitted,
Farjami & Farjami LLP

Dated: 3/9/05

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FORM PTO-1449 LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 0180144	SERIAL NO. 10/643,461
	APPLICANTS: Xiang, et al.	
	FILING DATE: August 18, 2003	GROUP ART: 2815

U.S. PATENT DOCUMENTS							
Exam. Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	1	6,262,462	7/17/2001	Marshall, et al.			
	2	5,721,145	2/24/1998	Kusakabe, et al.			
	3	2002/093046 A1	7/18/2002	Moriya, et al.			

FOREIGN PATENT DOCUMENTS								
Exam. Initials		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
	1	WO 2004/112147 A1	12/23/2004	WIPO				
	2	EP 1 164 636 A2	12/19/2001	EPO				
	3	JP 05082777	4/2/1993	JPO				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
	1	Ota et al, <i>Novel Locally Strained Channel Technique for High Performance 55nm CMOS</i> , IEDM Technical Digest, 27-30 (2002)
	2	<i>Applying Mechanical Stress to Improve MOS Semiconductor Performance</i> , 30 IBM Technical Disclosure Bulletin, 330-333 (1988)
	3	Momose et al, <i>Relationship Between Mobility and Residual-Mechanical-Stress As Measured By Raman Spectroscopy For Nitrided-Oxide-Gate MOSFETs</i> , 90 IEDM, 65-68 (1990)
	4	Jennifer O'Connor, <i>Analytical Predictions of Thermal Stress in MOSFETs</i> , IEEE, 131-143 (1995)
	5	Wristers et al, <i>Ultra Thin Oxide Reliability: Effects of Gate Doping Concentration and Poly-Si/SiO2 Interface Stress Relaxation</i> , IEEE, 77-83 (1996)
	6	Steege et al, <i>Silicide-induced Stress In Si: Origin and Consequences for MOS Technologies</i> , 38 Materials Science and Engineering R: Reports, 1-53 (2002)

EXAMINER:	DATE CONSIDERED:
EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant. Information Disclosure Statement-- Section 9 PTO-1449	